

L Number	Hits	Search Text	DB	Time stamp
1	329	396/611 118/052	USPAT	2004/06/24 11:34
2	1432	430/396	USPAT	2004/06/24 11:35
3	2081	430/296	USPAT	2004/06/24 11:35
4	2408	(396/611 118/052) 430/296	USPAT	2004/06/24 11:35
5	2	5025280.pn. 6575645.pn.	USPAT	2004/06/24 11:40
6	3750	((396/611 118/052) 430/296) 430/396	USPAT	2004/06/24 11:40
8	459	((396/611 118/052) 430/296) 430/396) and (polish\$3 planariz\$5)	USPAT	2004/06/24 11:41
9	462	((396/611 118/052) 430/296) 430/396) and CMP) (((396/611 118/052) 430/296) 430/396) and (polish\$3 planariz\$5))	USPAT	2004/06/24 11:41
10	1095	((396/611 118/052) 430/296) 430/396) and (processor computer memory)	USPAT	2004/06/24 11:41
11	3	((396/611 118/052) 430/296) 430/396) and (processor computer memory)) and (spectrophotometry reflectometry)	USPAT	2004/06/24 11:54
7	83	((396/611 118/052) 430/296) 430/396) and CMP	USPAT	2004/06/24 13:21
12	1835	"UV/vis spectrophotometry" scatterometry ellipsometry "x-ray reflectometry"	USPAT	2004/06/24 11:56
13	131	("UV/vis spectrophotometry" scatterometry ellipsometry "x-ray reflectometry") and (develop\$3 same resist)	USPAT	2004/06/24 11:57
14	88	("UV/vis spectrophotometry" scatterometry ellipsometry "x-ray reflectometry") and (develop\$3 same resist)) and ("process controller" computer memory)	USPAT	2004/06/24 13:09
15	50	trim adj etch\$3	USPAT	2004/06/24 13:09
16	37	(trim adj etch\$3) and (lithography resist)	USPAT	2004/06/24 13:10
17	9126	(cmp polish\$3 planariz\$4) and develop\$3 and resist	USPAT	2004/06/24 13:22
18	459	(cmp polish\$3 planariz\$4) same (develop\$3 with resist)	USPAT	2004/06/24 13:22
19	163	(cmp polish\$3 planariz\$4) with (develop\$3 with resist)	USPAT	2004/06/24 13:22
-	76	"5905020" "5840199" "5756256" "6221562" "6107172" "5294291" "4224361" "4119483"	USPAT	2004/06/24 11:33
-	132	"5905020" "5840199" "5756256" "6221562" "6107172" "5294291" "4224361" "4119483" "5033998"	USPAT	2003/09/30 13:57
-	78	coat\$3 and resist and (pattern\$3 develop\$3) and (elipsometry "uv/vis" "xray reflectometry")	USPAT	2003/09/30 14:00
-	24	(coat\$3 and resist and (pattern\$3 develop\$3) and (elipsometry "uv/vis" "xray reflectometry")) and (processor computer microprocessor)	USPAT	2003/09/30 14:02
-	452	156/345.22 156/345.13 156/345.24 156/345.12	USPAT	2003/09/30 14:26
-	0	"trim etchant"	USPAT	2003/09/30 14:26
-	235	trim with etch\$3	USPAT	2003/09/30 14:27
-	1	6589869.pn.	USPAT	2003/10/01 14:53
-	1	6413867.pn.	USPAT	2003/10/01 14:53